

Dual Operational Transconductance Amplifiers With Linearizing Diodes and Buffers

DESCRIPTION

The LM13700MX/NOPB-CN series consists of two current-controlled transconductance amplifiers, each with differential inputs and a push-pull output. The two amplifiers share common supplies but otherwise operate independently. Linearizing diodes are provided at the inputs to reduce distortion and allow higher input levels. The result is a 10-dB signal-to-noise improvement referenced to 0.5 percent THD. High impedance buffers are provided which are especially designed to complement the dynamic range of the amplifiers. The output buffers of the LM13700M differ from those of the LM13700MX/NOPB-CN in that their input bias currents (and thus their output DC levels) are independent of IABC. This may result in performance superior tothat of the LM13700MX/NOPB-CN in audio applications.

FEATURES

- gm Adjustable Over 6 Decades
- Excellent gm Linearity
- Excellent Matching Between Amplifiers
- Linearizing Diodes for reduced output distortion
- High Impedance Buffers
- High Output Signal-to-Noise Ratio

APPLICATIONS

- Current-Controlled Amplifiers
- Stereo Audio Amplifiers
- Current-Controlled Impedances
- Current-Controlled Filters
- Current-Controlled Oscillators
- Multiplexers
- Sample-and-Hold Circuits

Pin Configuration





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Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

PARAMETER		MIN	ΜΑΧ	UNIT
\mathbf{C} and \mathbf{M} there \mathbf{M} \mathbf{M} \mathbf{M}	Single-supply		+36	V
Supply Voltage, Vs=(V+) - (V-)	Dual-supply	-18	+18	V
DC Input Voltage	-Vs	+Vs	V	
Differential input voltage	-5	+5	V	
Diode bias current (I_D)			2	mA
Amplifier bias current (I _{ABC})		2	mA	
Buffer output current(I _{Buffer}) ⁽²⁾			20	mA
Output short circuit duration		Continuous		
Storage temperature(Ts)		-65	+150	C

Note 1: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

Note 2: Buffer output current should be limited so as to not exceed package dissipation.

Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

PARAMETER	MIN	ТҮР	ΜΑΧ	UNIT
V _s (single-supply configuration)	10		32	V
V+ (dual-supply configuration)	5		16	V
V- (dual-supply configuration)	-16		-5	V
Operating Temperature Range(T _A)	-20		85	C





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ELECTRICAL CHARACTERISTICS

(These specifications apply for V_S= \pm 15V, T_A=25 °C, I_{ABC}=500µA, pins 2 and 15 open unless otherwise specified. The inputs to the buffers are grounded and outputs are open.)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	МАХ	UNIT
		Over specified temperature range		0.4	4	mV
Input offset voltage	Vos	I _{ABC} =5uA		0.3	4	mV
Vos including diodes	V _{OS_D}	Diode bias current (I _D)=500 μ A		0.5	5	mV
Input offset change	ΔV _{os}	5uA≤I _{ABC} ≤500uA		0.1	3	mV
Input offset current	I _{OS}			0.1	0.6	uA
				0.4	5	uA
Input bias current	IB	Over specified temperature range		1	8	uA
E	gm	Take 10mV and 25mV to calculate	6700	9600	13000	μS
Forward transconductance		Over specified temperature range	5400			μS
gm tracking	gm_t			0.3		dB
		RL=0, I _{ABC} =5uA		5		uA
Peak output current	Ipk	R _L =0, I _{ABC} =500uA	350	500	650	uA
		R _L =0, Over specified temperature range	300			uA
Supply current	I _{CC}	I _{ABC} =500uA, both channels		2.2		mA
Common-mode range	Vic		±12	±13.5		v
Common-mode rejection ratio	CMRR		80	110		dB
Crosstalk	Crosstalk	Referred to input ⁽¹⁾ , 20Hz <f<20khz< td=""><td></td><td>100</td><td></td><td>dB</td></f<20khz<>		100		dB
Differential input current	Id	I _{ABC} =0, input=±4V		0.02	100	nA
Leakage current	I _{LEAK}	I _{ABC} =0(refer to test circuit)		0.2	100	nA
Input resistance	Z _{IN}		10	26		kΩ
Open-loop bandwidth	BW			2		MHz
Slew rate	SR	Unity gain compensated		50		V/µs
Buffer input current	I _{BIN}	See ⁽¹⁾		0.5	2	uA
Peak buffer output voltage	Ipkout-buf	See ⁽¹⁾	10			v
PEAK OUTPUT VOLTAGE						
Positive	V _{OP}	R _L =∞, 5uA≤I _{ABC} ≤500uA	12	14.2		v
Negative	V _{ON}	R _L =∞, 5uA≤I _{ABC} ≤500uA	-12	-14.4		V
Vos SENSITIVITY						
Positive		ΔVos/ΔV+		20	150	μ٧/٧
Negative		ΔVos/ΔV-		20	150	μV/V

(1) These specifications apply for V_s= \pm 15V, I_{ABC}=500µA, R_{OUT}=5k Ω connected from the buffer output to -V_s and the input of the buffer is connected to the transconductance amplifier output.



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TYPICAL CHARACTERISTICS



Figure 1. Input Offset Voltage vs IABC



Figure 3. Input BIAS Current vs IABC



Figure 5. Leak Current vs Temperature



Figure 7. Amplifier Bias Voltage vs I_{ABC}



Figure 2. Input Offset Current vs IABC



Figure 4. Peak Output Current vs IABC



Figure 6. Input Leak Current vs Input Different Voltage



Figure 8. Output Voltage vs IABC





Dual Operational Transconductance Amplifiers With Linearizing Diodes and Buffers

Detailed Description

Overview

The LM13700MX/NOPB-CN is a two channel current controlled differential input transconductance amplifier with additional output buffers. The inputs include linearizing diodes to reduce distortion, and the output current is controlled by a dedicated pin.

The outputs can sustain a continuous short to ground.

Functional Block Diagram



Figure 9. One Operational Transconductance Amplifier

(1) Feature Description

The differential transistor pair Q_4 and Q_5 form a transconductance stage in that the ratio of their collector currents is defined by the differential input voltage according to the transfer function:

$$V_{IN} = \frac{kT}{q} ln_{l_a}^{l_5}$$
(1)

where V_{IN} is the differential input voltage, kT/q is approximately 26 mV at 25 $^{\circ}$ C and I₅ and I₄ are the collector currents of transistors Q₅ and Q₄ respectively. With the exception of Q₁₂ and Q₁₃, all transistors and diodes are identical in size. Transistors Q₁ and Q₂ with Diode D1 form a current mirror which forces the sum of currents I₄ and I₅ to equal I_{ABC}:

$$I_4 + I_5 = I_{ABC}$$
 (2)

where $I_{\mbox{\scriptsize ABC}}$ is the amplifier bias current applied to the gain pin.

For small differential input voltages the ratio of I_4 and I_5 approaches unity and the Taylor series of the In function is approximated as:

$$\frac{kT}{q} \ln \frac{I_5}{I_4} = \frac{kT}{q} \frac{I_5 \cdot I_4}{I_4}$$

$$I_4 \approx I_5 \approx \frac{I_{ABC}}{2}$$
(3)

$$V_{\rm IN} \left[\frac{I_{\rm ABC}^{\rm q}}{2 {\rm kT}} \right] = I_5 - I_4 \tag{4}$$



LM13700MX/NOPB-CN Dual Operational Transconductance Amplifiers With Linearizing Diodes and Buffers

Collector currents I_4 and I_5 are not very useful by themselves and it is necessary to subtract one current from the other. The remaining transistors and diodes form three current mirrors that produce an output current equal to I_5 minus I_4 thus:

$$V_{\rm IN} \left[\frac{I_{\rm ABC}^{\rm q}}{2kT} \right] = I_{\rm OUT}$$
(5)

The term in brackets is then the transconductance of the amplifier and is proportional to IABC.

(2) Linearizing Diodes

For differential voltages greater than a few millivolts, Equation 3 becomes less valid and the transconductance becomes increasingly nonlinear. Figure 10 demonstrates how the internal diodes can linearize the transfer function of the amplifier. For convenience assume the diodes are biased with current sources and the input signal is in the form of current I_S . Since the sum of I_4 and I_5 is I_{ABC} and the difference is I_{OUT} , currents I_4 and I_5 is written as follows:

$$I_4 = \frac{I_{ABC}}{2} - \frac{I_{OUT}}{2}$$
, $I_5 = \frac{I_{ABC}}{2} + \frac{I_{OUT}}{2}$ (6)

Since the diodes and the input transistors have identical geometries and are subject to similar voltages and temperatures, the following is true:

$$\frac{kT}{q} \ln \frac{\frac{I_D}{2} + I_S}{\frac{I_D}{2} - I_S} = \frac{kT}{q} \ln \frac{\frac{I_{ABC}}{2} - \frac{I_{OUT}}{2}}{\frac{I_{ABC}}{2} - \frac{I_{OUT}}{2}}$$

$$\therefore I_{OUT} = I_S(\frac{2I_{ABC}}{I_D}) \text{ for } |I_S| < \frac{I_D}{2}$$
(7)

Notice that in deriving Equation 7 no approximations have been made and there are no temperature-dependent terms. The limitations are that the signal current not exceed $I_D/2$ and that the diodes be biased with currents. In practice, replacing the current sources with resistors will generate insignificant errors.

(3) Device Functional Modes

Use in single ended or dual supply systems requires minimal changes. The outputs can support a sustained short to ground. Note that use of the LM13700MX/NOPB-CN in 5 V supply systems requires will reduce signal dynamic range.

this is due to the PNP transistors having a higher VBE than the NPN transistors.

(4) Output Buffers

Each channel includes a separate output buffer which consists of a Darlington pair transistor that can drive up to 20mA.



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Application and Implementation

Application Information

An OTA is a versatile building block analog component that can be considered an ideal transistor. The LM13700MX/NOPB-CN can be used in a wide variety of applications, from voltage controlled amplifiers and filters to VCOs. The 2 well matched, independent channels make the LM13700MX/NOPB-CN well suited for stereo audio applications.

Typical Application



Figure 10 . Voltage Controlled Amplifier

(1) Design Requirements

For this example application, the system requirements provide a volume control for a 1 V_P input signal with a THD<0.1% using \pm 15V supplies. The volume control varies between -13 V and 15 V and needs to provide an adjustable gain range of >30dB.

(2) Detailed Design Procedure

Using the linearizing diodes is recommended for most applications, as they greatly reduce the output distortion. It is required that the diode bias current, I_D be greater than twice the input current, I_s . As the input voltage has a DC level of 0V, the Diode Bias input pins are 1 diode drop above 0V, which is +0.7V. Tying the bias to the clean V+ supply, results in a voltage drop of 14.3V across R_D . Using the recommended 1mA for I_D is appropriate here, and with V_S =+15 V, the voltage drop is 14.3V, and so using the standard value of 13k Ω is acceptable and will provide the desired gain control.

To obtain the <0.1% THD requirement, the differential input voltage must be <60mV_{PP} when the linearizing diodes are used. The input divider on the input will reduce the $1V_P$ input to $33mV_{PP}$, which is within the desired spec.

Next, set I_{BIAS} . The Bias Input pins (pins 1 or 16), are 2 diode drops above the negative supply, and therefore $V_{BIAS}=2(V_{BE})+V$ -, which for this application is -13.6V. To set I_{BIAS} to 1mA when $V_C=15V$ requires a 28.6k Ω ; 30k Ω is a standard value and is used for this application. The gain will be linear with the applied voltage.



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(3) Application Curve



Figure 11 . Signal Amplitude vs Control Voltage

System Examples - Voltage-Controlled Amplifiers

Figure 13 shows how the linearizing diodes is used in a voltage-controlled amplifier. To understand the input biasing, it is best to consider the $13k\Omega$ resistor as a current source and use a Thevenin equivalent circuit as shown in Figure 14. This circuit is similar to Figure 12 and operates the same. The potentiometer in Figure 14 is adjusted to minimize the effects of the control signal at the output.



Figure 12 . Linearizing Diodes

For optimum signal-to-noise performance, I_{ABC} should be as large as possible as shown by the Output Voltage vs Amplifier Bias Current graph. Larger amplitudes of input signal also improve the S/N ratio. The linearizing diodes help here by allowing larger input signals for the same output distortion as shown by the Distortion vs. Differential Input Voltage graph. S/N may be optimized by adjusting the magnitude of the input signal via R_{IN} (Figure 13) until the output distortion is below the desired level. The output voltage swing can then be set at any level by selecting R_L .

Although the noise contribution of the linearizing diodes is negligible relative to the contribution of the amplifier's internal transistors, I_D should be as large as possible. This minimizes the dynamic junction resistance of the diodes (r_e) and maximizes their linearizing action when balanced against R_{IN} . A value of 1mA is recommended for I_D unless the specific application demands otherwise.



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Figure 13. Voltage-Controlled Amplifier

Other Applications



Figure 15. Stereo Volume Control



Figure 17. Voltage-Controlled Low-Pass Filter



Figure 19. Amplitude Modulator



Figure 14. Equivalent VCA Input Circuit



Figure 16. Sinusoidal VCO



Figure 18. Voltage-Controlled Hi-Pass Filter



Figure 20. Triangular/Square-Wave VCO



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Figure 21. Multiplexer



Figure 23. Sample-Hold Circuit



Figure 22. Phase Lock Loop



Figure 24. Unity Gain Follower

Test Circuits



Figure 25. Leakage Current Test Circuit



Figure 26. Differential Input Current Test Circuit



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PACKAGE OUTLINE DIMENSIONS

SOP16



SYMBOL	MILLIMETER				MILLIMETER		
	MIN	NOM	MAX	SYMBOL	MIN	NOM	МАХ
А	-	-	1.75	E	3.80	3.90	4.00
A1	0.10	-	0.25	E1	5.80	6.00	6.20
A2	1.35	1.45	1.55	е	1.27 BSC		
A3	0.60	0.65	0.70	h	0.30	-	0.50
b	0.35	-	0.50	L	0.40	-	0.80
с	0.19	-	0.25	θ	0°	-	8°
D	9.80	9.90	10.00				



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